## Features

- Reference Oscillator up to 15 MHz
- Two Programmable 16-bit Dividers Adjustable from 2 to 65535
- Fine Tuning Steps

   AM ≥ 1 kHz
  - $FM \ge 2 kHz$
- Four Programmable Switching Outputs (Open Drain up to 15 V)
- Integrated Loop-push-pull Stage for AM/FM
- High Signal/Noise Ratio



AM/FM PLL with 4 Switches

# U4285BM

# Description

The U4285BM is an integrated circuit in BICMOS technology for frequency synthesizers. It performs all the functions of a PLL radio tuning system and is controlled by a 2-wire bus. The device is designed for all frequency synthesizer applications in radio receivers, as well as for RDS (Radio Data System) applications.

Figure 1. Block Diagram



Rev. 4750A-AUDR-11/03





## **Pin Configuration**



### Figure 2. Pinning SSO20

## **Pin Description**

Pin	Symbol	Function
1	V <sub>DD</sub>	Supply voltage
2	SCL	Bus clock
3	SDA	Bus data
4	AS	Address selection
5	SWO1	Switching output 1
6	SWO2	Switching output 2
7	SWO3	Switching output 3
8	SWO4	Switching output 4
9	FMOSC	FM oscillator input
10	GND2	Ground 2 (analog)
11	AMOSC	AM oscillator input
12	PDFMO	FM analog output
13	PDFM	FM current output
14	PDAM	AM current output
15	PDAMO	AM analog output
16	VA	Analog supply voltage
17	С	Capacitor
18	OSCIN	Oscillator input
19	OSCOUT	Oscillator output
20	GND1	Ground 1 (digital)

U4285BM

# Functional Description

The U4285BM is controlled via the 2-wire bus. One module address byte, two subaddress bytes and five data bytes enable programming.

The module address contains a programmable address bit A 1, which (along with address select input AS, pin 4), enables the operation of two U4285BM devices in one system. If bit A 1 is identical with the status of the address select input AS, the chip is selected.

The subaddress determines which of the data bytes is transmitted first. If the subaddress of the R-divider is transmitted, the sequence of the next data bytes is DB 0 (status), DB 1 and DB 2. If the subaddress of the N-divider is transmitted, the sequence of the next data bytes is DB 3 and DB 4. The bit organization of the module address, subaddress and 5 data bytes is shown in table "Bit Organization" on page 7.

Each transmission on the bus begins with the "START" condition and has to be ended by the "STOP" condition (see Table "Transmission Protocol" on page 7).

The integrated circuit U4285BM has two separate inputs for the AM and FM oscillators. Pre-amplified AM and FM signals are fed to the 16 bit N-divider via the AM/FM switch. The AM/FM switch is software controlled. Tuning steps can be selected by the 16 bit R-divider.

Furthermore, the device provides a digital memory phase detector and two separate current sources for AM and FM amplifiers (charge pump) as given in the Table "Electrical Characteristics" on page 4. The separate current sources (charge pumps) allow independent gain adjustment, providing high current for high-speed tuning and low current for stable tuning.

### **Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Parameters	Pins	Symbol	Value	Unit
Supply voltage	1	V <sub>DD</sub>	-0.3 to +6	V
Input voltage	2, 3, 4, 9, 11, 18, 19	VI	-0.3 to V <sub>DD</sub> + 0.3	V
Output current	3, 5, 6, 7, 8	Ι <sub>ο</sub>	-1 to +5	mA
Output drain voltage	5, 6, 7, 8	V <sub>OD</sub>	15	V
Analog supply voltage with 220 $\Omega\text{serial}$ resistance 2 minutes^{(1)}	16	V <sub>A</sub> V <sub>A</sub>	6 to 15 24	V V
Output current	12, 15	I <sub>AO</sub>	-1 to +20	mA
Ambient temperature range		T <sub>amb</sub>	-30 to +85	°C
Storage temperature range		T <sub>stg</sub>	-40 to +125	°C
Junction temperature		Tj	125	° C
Electrostatic handling (modified MIL STD 883 D method 3015.7: all supply pins connected together)		±V <sub>ESD</sub>	1000	V

Note: 1. Corresponding to the application circuit (Figure 8 on page 8)





# **Thermal Resistance**

Parameters	Symbol	Value	Unit
Junction ambient	R <sub>thJA</sub>	160	K/W

## **Electrical Characteristics**

Parameters	Test Conditions	Pins	Symbol	Min.	Тур.	Max.	Unit
Supply voltage		1	V <sub>DD</sub>	4.5	5.0	5.5	V
Quiescent supply current	AM mode/FM mode	1	I <sub>DD</sub>		4.0	7.0	mA
FM input sensitivity,	f <sub>i</sub> = 70 to 120 MHz	9	V <sub>SFM</sub>	40			mV <sub>rms</sub>
$R_{g} = 50 $ Ω, FMOSC	f <sub>i</sub> = 160 MHz	9	$V_{SFM}$	150			mV <sub>rms</sub>
AM input sensitivity, $R_G = 50 \Omega$ , AMOSC	f <sub>i</sub> = 0.6 to 35 MHz	11	$V_{SAM}$	40			mV <sub>rms</sub>
Oscillator input sensitivity, $R_G = 50 \ \Omega$ , OSCIN	f <sub>i</sub> = 0.1 to 15 MHz	18	V <sub>SOSC</sub>	100			mV <sub>rms</sub>
Switching Output SWO1, SWO2, S	WO3, SWO4 (Open Drain)						
Output voltage LOW	I <sub>L</sub> = 1 mA	5, 6, 7, 8	V <sub>SWOL</sub>		100	400	mA
Output leakage current HIGH	V5, V6, V7, V8 = 10 V	5, 6, 7, 8	I <sub>OHL</sub>			100	nA
Phase Detector PDFM				1	1	1	
Output current 1		13	±I <sub>PDFM</sub>	1600	2000	2400	μA
Output current 2		13	±I <sub>PDFM</sub>	400	500	600	μA
Leakage current		13	±I <sub>PDFML</sub>			20	nA
Phase Detector PDAM							
Output current 1		14	±I <sub>PDAM</sub>	160	200	240	μA
Output current 2		14	±I <sub>PDAM</sub>	40	50	60	μA
Leakage current		14	±I <sub>PDAML</sub>			20	μA
Analog Output PDFMO, PDAMO							
Saturation voltage LOW	l = 15 mA	12, 15	V <sub>satL</sub>		200	400	mW
Saturation voltage HIGH	l = 15 mA	12, 15	V <sub>satH</sub>	9.5	9.95		V
Bus SCL, SDA, AS		ILIL					
Input voltage HIGH		2, 3, 4	V <sub>iBUS</sub>	3.0		V <sub>DD</sub>	V
Input voltage LOW		2, 3, 4	V <sub>iBUS</sub>	0		1.5	V
Output voltage acknowledge LOW	I <sub>SDA</sub> = 3 mA	3	Vo			0.4	V
Clock frequency		2	f <sub>SCL</sub>			100	kHz
Rise time SDA, SCL		2, 3	t <sub>r</sub>			1	μs
Fall time SDA, SCL		2, 3	t <sub>f</sub>			300	ns
Period of SCL HIGH	HIGH	2	t <sub>H</sub>	4.0			μs
Period of SCL LOW	LOW	2	tL	4.7			μs

## **Electrical Characteristics (Continued)**

 $V_{DD} = 5 \text{ V}, \text{ V}_{A} = 10 \text{ V}, \text{ T}_{amb} = 25^{\circ} \text{ C}, \text{ unless otherwise specified}$ 

Parameters	Test Conditions	Pins	Symbol	Min.	Тур.	Max.	Unit
Set-up Time							
Start condition			t <sub>sSTA</sub>	4.7			μs
Data			t <sub>sDAT</sub>	250			μs
Stop condition			t <sub>sSTOP</sub>	4.7			μs
Time space <sup>(1)</sup>			t <sub>wSTA</sub>	4.7			μs
Hold Time		L. L					
Start condition			t <sub>hSTA</sub>	4.0			μs
DATA			t <sub>hDAT</sub>	0			μs

Note: 1. This is a period of time where the bus must be free from data transmission before a new transmission can be started.

Figure 3. FM Input Sensitivity,  $T = 85^{\circ}C$ 



Figure 4. FM Input Sensitivity, T = -30° C







**Figure 5.** AM Input Sensitivity,  $T = 85^{\circ}C$ 



Figure 6. AM Input Sensitivity,  $T = -30^{\circ} C$ 



Figure 7. Bus Timing



# **Bit Organization**

	MSB							LSB	
	1	1	0	0	1	0	0/1	0	
Module address	A7	A6	A5	A4	A3	A2	A1	A0	
Subaddress (R-divider)	Х	Х	Х	0	0	1	Х	Х	
Subaddress (N-divider)	Х	Х	Х	Х	1	1	Х	Х	
Data buta 0 (Statua)	SWO1	SWO2	SWO3	SWO4	AM/FM	PD - ANA	PD - POL	PD - CUR	
Data byte 0 (Status)	D7	D6	D5	D4	D3	D2	D1	D0	
Data byte 1	2 <sup>15</sup>			R-di	vider			2 <sup>8</sup>	
Data byte 2	27		R-divider						
Data byte 3	2 <sup>15</sup>		N-divider						
Data byte 4	2 <sup>7</sup>			N-di	vider			2 <sup>0</sup>	

### Table 1. Function Mode

Bit Description	Description Mode		HIGH	
D3	AM/FM	FM operation	AM operation	
D2	PD - ANA	PD analog	TEST	
D1	PD - POL	Negative polarity	Positive polarity	
D0	PD - CUR	Output current 2	Output current 1	

## **Transmission Protocol**

	MSB	LSB										
S	Add	ress	Α	Subaddress	Α	Data 0	Α	Data 1	Α	Data 2	Α	Р
	A0	A7		R-divider								

	MSB	LSB								
S	Add	ress	Α	Subaddress	Α	Data 3	Α	Data 4	Α	Р
	A0	A7		N-divider						

Note: S = Start, P = Stop, A = Acknowledge





### Figure 8. Application Circuit



# Recommendations for Applications

U4285BM

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- $C_3 = 100 \text{ nF}$  should be very close to pin 1 ( $V_{DD}$ ) and pin 20 (GND 1)
- GND 2 (pin 10 analog ground) and GND 1 (pin digital ground) must be connected according to Figure 8
- 4 MHz crystal must be very close to pin 18 and pin 19
- Components of the charge pump ( $C_1/R_1$  for AM and  $C_2/R_2$  for FM) should be very close to pin 14 with respect to pin 13

Figure 9. PCB Layout



# **Ordering Information**

Extended Type Number	Package	Remarks
U4285BM-MFS	SSO20 plastic	-
U4285BM-MFSG3	SSO20 plastic	Taping according to IEC-286-3

## **Package Information**







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